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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**Filed: November 29, 2007

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Sheet 1 of 3

Complete if Known

Application Number	Unassigned
Filing Date	
First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	049411-0340

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
	A30	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003		
	A31	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003		
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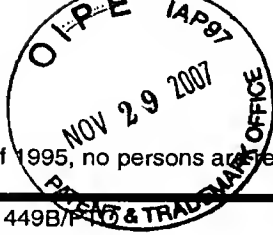
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Substitute for form 1449B/P-10 & TRADEMARK OFFICE		Complete if Known	
		Application Number	Unassigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT Filed: <u>November 29, 2007</u> (use as many sheets as necessary)		Filing Date	
		First Named Inventor	Igor BARGATIN et al.
		Group Art Unit	Unassigned
		Examiner Name	Unassigned
		Attorney Docket Number	049411-0340
Sheet	2	of	3

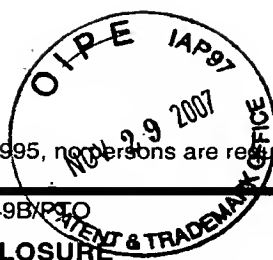
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NON PATENT LITERATURE DOCUMENTS			
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